FAIRCHILD SEMICONDUCTOR®

August 2010

FDMC3612

N-Channel Power Trench® MOSFET

100 V, 12 A, 110 mΩ

Features

- Max $r_{DS(on)}$ = 110 mΩ at V_{GS} = 10 V, I_D = 3.3 A
- Max $r_{DS(on)}$ = 122 mΩ at V_{GS} = 6 V, I_D = 3.0 A
- Low Profile - 1 mm max in Power 33
- 100% UIL Tested
- RoHS Compliant

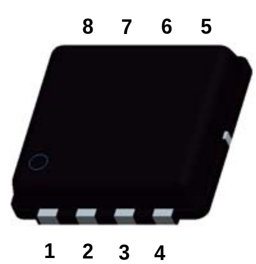
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

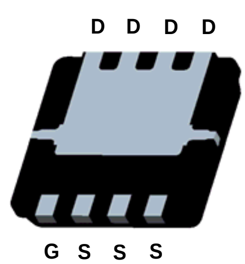
Applications

- DC - DC Conversion
- PSE Switch

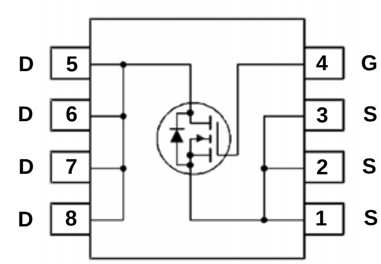
Top



Bottom



MLP 3.3x3.3



MOSFET Maximum Ratings T_C = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) T_C = 25 °C	16	A
	-Continuous (Silicon limited) T_C = 25 °C	12	
	-Continuous T_A = 25 °C (Note 1a)	3.3	
	-Pulsed	15	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	32	mJ
P_D	Power Dissipation T_C = 25 °C	35	W
	Power Dissipation T_A = 25 °C (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to + 150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC3612	FDMC3612	Power 33	13"	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		109		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	2.5	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-7		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 3.3 A		92	110	mΩ
		V_{GS} = 6 V, I_D = 3.0 A		98	122	
		V_{GS} = 10 V, I_D = 3.3 A, T_J = 125 °C		177	212	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 3.3 A		13		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		662	880	pF
C_{oss}	Output Capacitance			40	55	pF
C_{rss}	Reverse Transfer Capacitance			23	35	pF
R_g	Gate Resistance			1.3		Ω

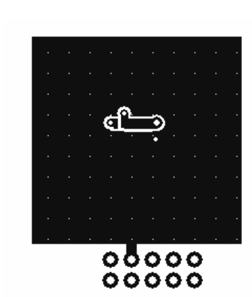
Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 3.3 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		7.4	15	ns
t_r	Rise Time			2.8	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	34	ns
t_f	Fall Time			2	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 3.3 A		14.4	21	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 5 V		7.9	12	nC
Q_{gs}	Total Gate Charge			2.3		nC
Q_{gd}	Gate to Drain "Miller" Charge			3.7		nC

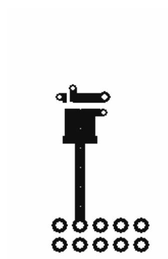
Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 3.3 A (Note 2)		0.88	1.2	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.77	1.2	
t_{rr}	Reverse Recovery Time	I_F = 3.3 A, di/dt = 100 A/μs		34	55	ns
Q_{rr}	Reverse Recovery Charge			37	60	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25 °C; N-ch: L = 1 mH, I_{AS} = 8 A, V_{DD} = 90 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

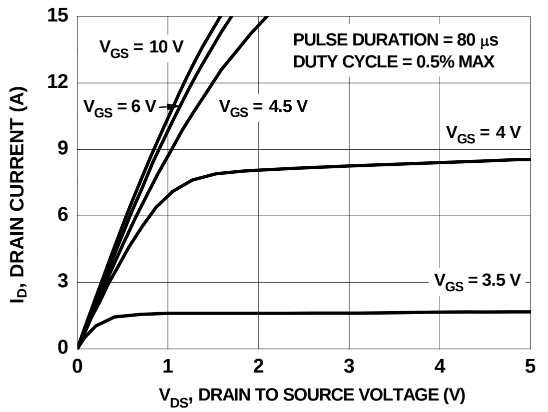


Figure 1. On Region Characteristics

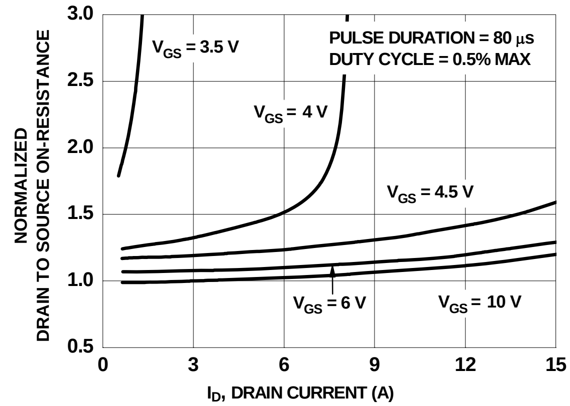


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

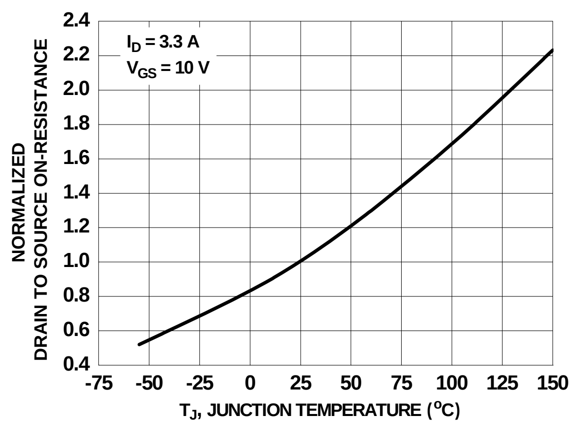


Figure 3. Normalized On Resistance vs Junction Temperature

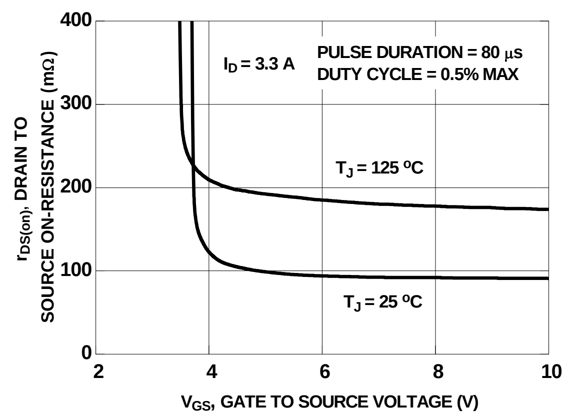


Figure 4. On-Resistance vs Gate to Source Voltage

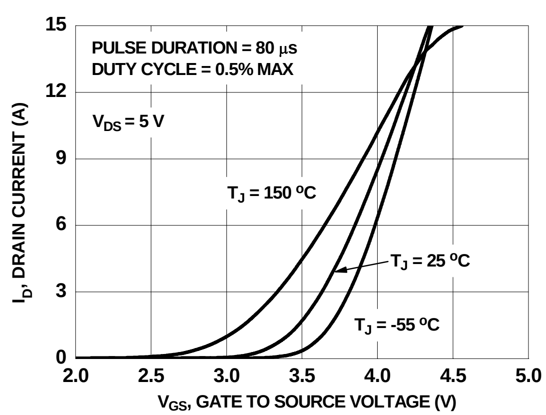


Figure 5. Transfer Characteristics

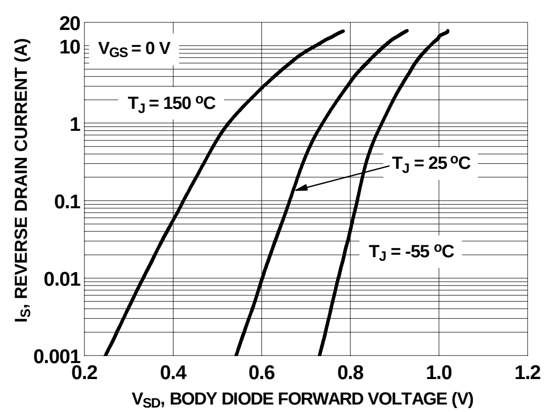


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

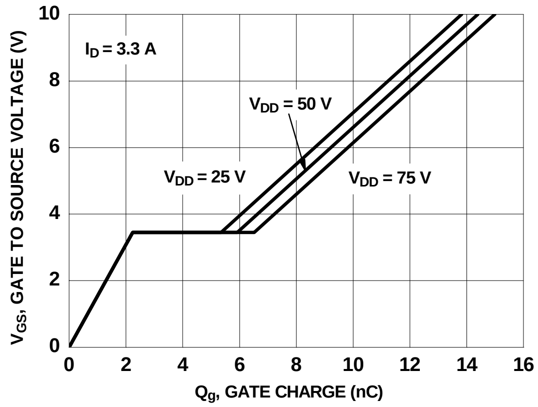


Figure 7. Gate Charge Characteristics

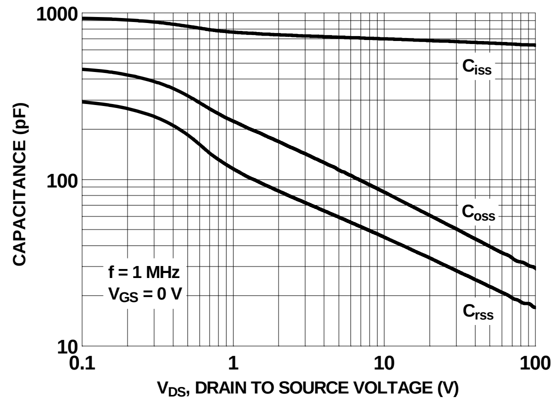


Figure 8. Capacitance vs Drain to Source Voltage

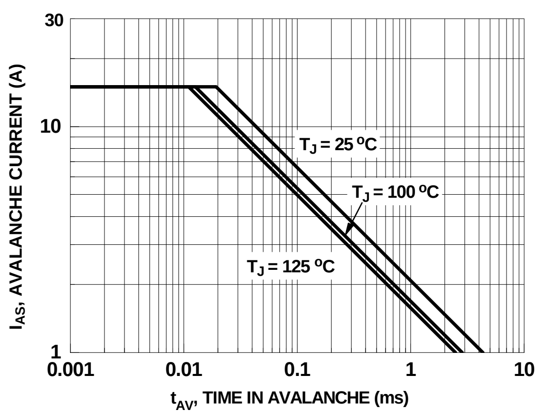


Figure 9. Unclamped Inductive Switching Capability

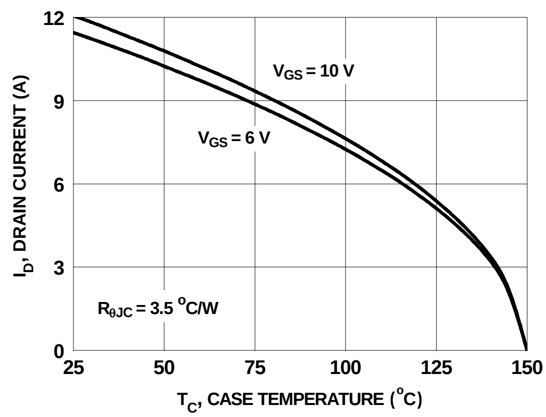


Figure 10. Maximum Continuous Drain Current vs Case Temperature

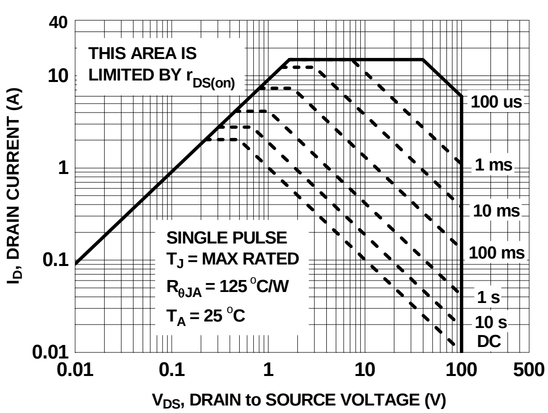


Figure 11. Forward Bias Safe Operating Area

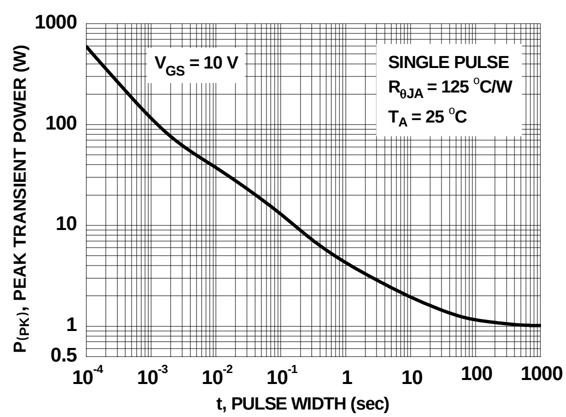


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

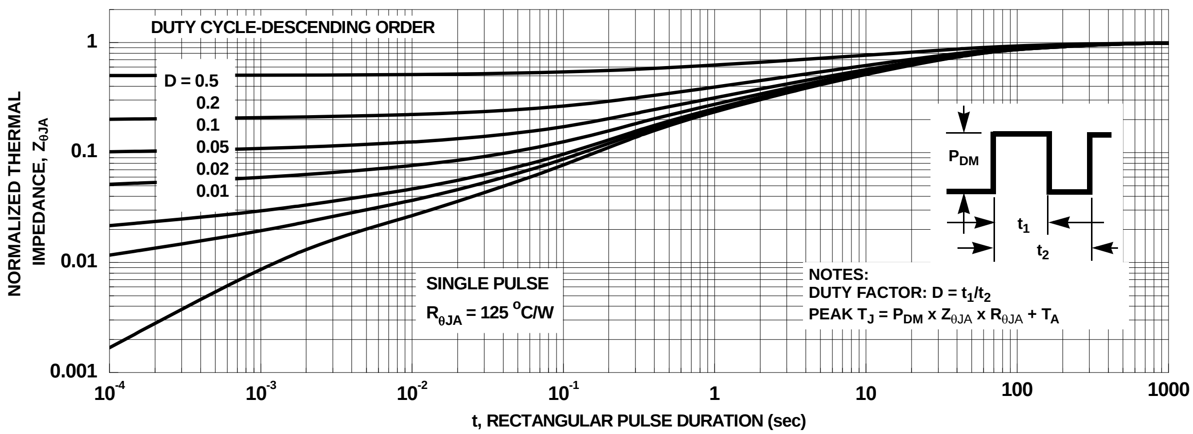
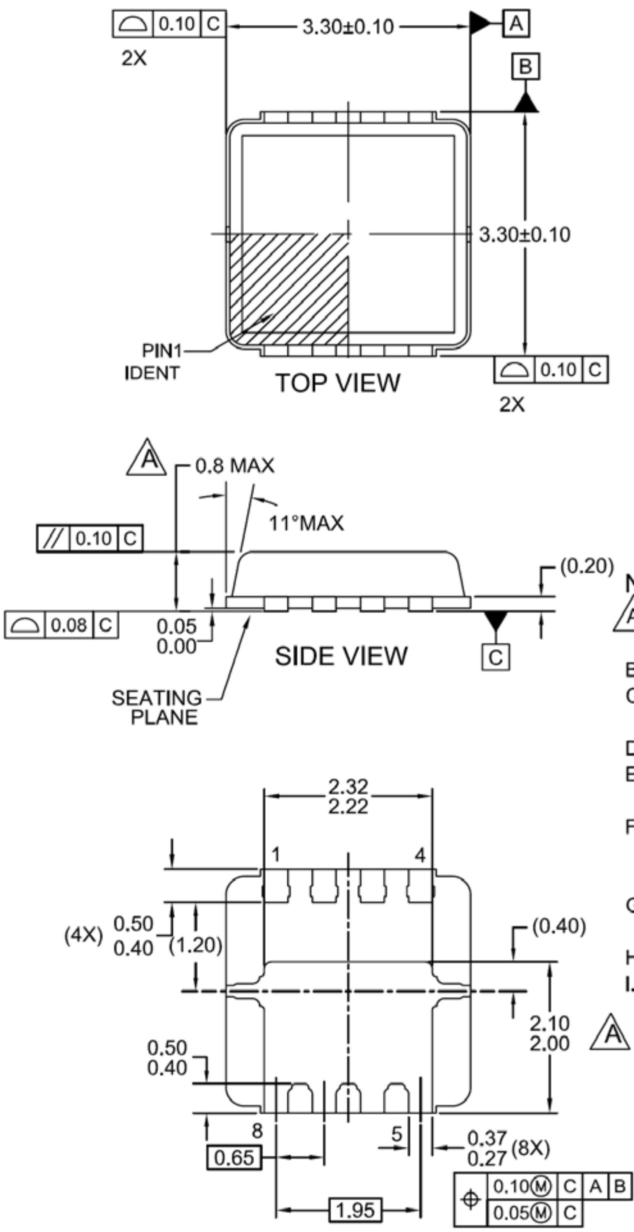
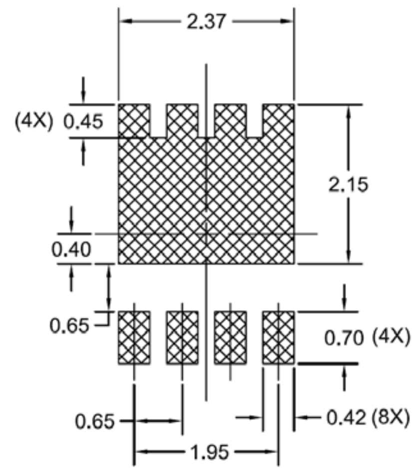


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout





RECOMMENDED LAND PATTERN

NOTES:

A. EXCEPT AS NOTED, PACKAGE CONFORMS TO JEDEC REGISTRATION MO-240 VARIATION BA..

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

D. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY

E. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS.

F. FLANGE DIMENSIONS INCLUDE INTERTERMINAL FLASH OR PROTRUSION. INTERTERMINAL FLASH OR PROTRUSION SHALL NOT EXCEED 0.25MM PER SIDE.

G. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.

H. DRAWING FILENAME: MKT-MLP08Trev1.

I. GENERAL RADII FOR ALL CORNERS SHALL BE 0.20MM MAX.

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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Rev. I48